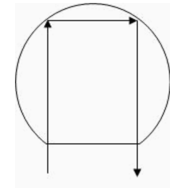
Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	200.00 +/- 0.50 mm	
	2.0	Notch Direction	{110}+/-1 degree	Wafer Vendor
	3.0	Notch or Flat	Notch	Wafer Vendor
	4.0	Secondary Flat Orientation	None	
	5.0	Overall Thickness	634.00 +/- 13.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	7.0	Bow	<199.00µm	Estimate spec. ADE to ASTM F534, 20%
	8.0	Warp	<199.00µm	Estimate spec. ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	13.0	Handle Thickness	550.00 +/- 10.00 µm	ADE, 100%
	14.0	Handle Doping Type	P	Wafer Vendor
	15.0	Handle Dopant	Boron	Wafer Vendor
	16.0	Handle Resistivity	<1 Ohmcm	Wafer Vendor
	17.0	Backside Finish	Polished with oxide and scribe	Guaranteed by Process
BuriedOxide	18.0	Oxide Type	Thermal	
	19.0	Oxide Thickness	20,000.00 +/- 2,000.00 A	Nanospec centre point, 4%
	20.0	Oxide formed on	Handle Wafer	
DeviceSilicon	21.0	Device Growth Method	CZ	Wafer Vendor
	22.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor
	23.0	Nominal Thickness	40.00 +/- 1.00 µm	FTIR, 100% 9-Pt (note3)
	24.0	Distance to device silicon edge from wafer edge	<= 2.0mm	Typical by Process
	25.0	Device Doping Type	P	Wafer Vendor
	26.0	Device Dopant	Boron	Wafer Vendor
	27.0	Device Resistivity	<1 Ohmcm	Wafer Vendor
BuriedOxide2	28.0	Oxide 2 Type	Thermal	
	29.0	Oxide 2 Thickness	20,000.00 +/- 2,000.00 A	Nanospec centre point measurement, 4%
DeviceSilicon2	30.0	Device 2 Growth Method	CZ	Wafer Vendor
	31.0	Device 2 Orientation	{100} +/- 1 degree	Wafer Vendor
	32.0	Device 2 Nominal Thickness	40.00 +/- 1.50 um	ADE Single point measurement (see note 3)

Part Number	Customer

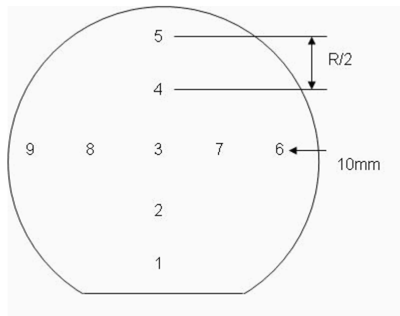
Category		Parameter	Specification	Measurement Method
DeviceSilicon2	33.0	Distance to Device 2 edge from wafer edge	< = 3mm	Guaranteed by Process
	34.0	Device 2 DopingType	P	Wafer Vendor
	35.0	Device 2 Dopant	Boron	Wafer Vendor
	36.0	Device 2 Resistivity	<1 Ohmcm	Wafer Vendor
DeviceSilicon	37.0	Voids	none	Wafer Vendor
	38.0	Scratches	0	Bright Light, 100% (note 2)
	39.0	Haze	none	Bright Light, 100% (note 2)

Part Number	Customer		
Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 200.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information